

# SANYO SEMICONDUCTOR

2SD995

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NPN Triple Diffused Mesa Type Silicon Transistor  
For H-Deflection Output with High Voltage (With Damper Diode)

## Absolute Maximum Ratings at Ta=25°C

Collector to Base Voltage	V <sub>CB0</sub>	2500	V
Collector to Emitter Voltage	V <sub>CE0</sub>	900	V
Emitter to Base Voltage	V <sub>EB0</sub>	6	V
Collector Current	I <sub>C</sub>	3	A
Collector Current (peak)	i <sub>cp</sub>	7	A
Collector Dissipation	P <sub>C</sub>	3	W
	P <sub>C</sub> T <sub>c</sub> =25°C	50	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-40~+150	°C

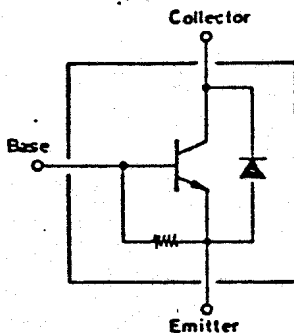
## Electrical Characteristics at Ta=25°C

		min	typ	max	unit
Collector Cut off Current	I <sub>CES</sub>			1.0	mA
Emitter Cut off Current	I <sub>EBO</sub>		40	130	mA
Emitter to Base Voltage	V <sub>EB0</sub>	6.0			V
Emitter to Collector Voltage	V <sub>ECO</sub>			2.0	V
DC Current Gain	h <sub>FE</sub>		3*	15*	
C-E Saturation Voltage	V <sub>CE(sat)</sub>			5	V
B-E Saturation Voltage	V <sub>BE(sat)</sub>			1.3	V
C-E Sustain Voltage	V <sub>CE(sus)</sub>	900			V
Fall Time	t <sub>f</sub>			1.0	μs

\* 2SD995 are classified according to 1.5A h<sub>FE</sub> as follows.

3 K 9 5 M 15

## Equivalent Circuit



## Case Outline (UNIT:mm)

